



VS10 Detector Set

Room temp fast 1x1 mm LWIR set, micro sized preamp, for < 2 to 11+ microns, DC to 10MHz.

- PVM-10.6-1x1
- uIP-DC-10M-S
- PPS-03

Photovoltaic multiple junction detectors PVM

PVM series features room temperature and TE cooled IR multiple junction photovoltaic detectors.

Detector type	Cooling, operating temperature $T [K]$	Optimal wavelength ^{*)} $\lambda_{opt} [\mu m]$	Detectivity ^{**)}		Current responsivity length product $R \cdot L \left[\frac{A \cdot mm}{W} \right]$	Time constant $\tau [ns]$	Resistance $R [\Omega]$	Acceptance angle ^{***)} $\Omega \left[\frac{1}{\text{sr}} \right]_{2NA}$	Optical area ^{****)} $[mm \times mm]$	Package	Window ^{*****)}
			$D^* \left[\frac{cm \cdot \sqrt{Hz}}{W} \right]$	$@\lambda_{peak}$							
PVM	uncooled, ~300	8	$\geq 1.2 \times 10^8$	$\geq 6.0 \times 10^7$	≥ 0.008	≤ 4	50 to 300	$\geq 90, 0.71$	0.1x0.1 0.2x0.2 1x1 2x2 3x3 4x4 ¹⁾	BNC, TO39	no window
		10.6	$\geq 2.0 \times 10^7$	$\geq 1.0 \times 10^7$	≥ 0.002	≤ 1.5	20 to 150				
	two-stage TE-cooled (2TE), ~230	8	$\geq 6.0 \times 10^8$	$\geq 3.0 \times 10^8$	≥ 0.015	≤ 4	150 to 1000	$\sim 70, 0.87$	TO8, TO66	wedged ZnSe AR coated	wedged ZnSe AR coated
		10.6	$\geq 2.0 \times 10^8$	$\geq 1.0 \times 10^8$	≥ 0.006	≤ 3	90 to 350				

^{*)} Other optimal wavelengths available upon request.

^{**) Data sheet states minimum guaranteed D^* values for each detector model. Higher performance detectors can be provided upon request.}

^{***)} Other optical area available upon request.

^{****)} Other windows available upon request.

¹⁾ Optical area available only for uncooled detectors.

Photovoltaic detectors optically immersed PVMI

PVMI series features room temperature and TE cooled IR multiple junction photovoltaic detectors, optically immersed (achieved by using high refractive index micro lenses) in order to improve performance of the devices, different acceptance angle and saturation level. Both PVM and PVMI devices are optimized for the maximum performance at opt. Highest performance and stability are achieved by application of variable gap HgCdTe semiconductor, optimized doping and sophisticated surface processing.

Detector type	Cooling, operating temperature $T [K]$	Optimal wavelength ^{*)} $\lambda_{opt} [\mu m]$	Detectivity ^{**)}		Current responsivity length product $R \cdot L \left[\frac{A \cdot mm}{W} \right]$	Time constant $\tau [ns]$	Resistance $R [\Omega]$	Acceptance angle ^{***)} $\Omega \left[\frac{1}{\text{sr}} \right]_{2NA}$	Optical area ^{****)} $[mm \times mm]$	Package	Window ^{*****)}
			$D^* \left[\frac{cm \cdot \sqrt{Hz}}{W} \right]$	$@\lambda_{peak}$							
PVMI	uncooled, ~300	8	$\geq 6.0 \times 10^8$	$\geq 3.0 \times 10^8$	≥ 0.04	≤ 4	50 to 300	$\sim 36, 1.62$	1x1 2x2	BNC, TO39	no window
		10.6	$\geq 2.0 \times 10^8$	$\geq 1.0 \times 10^8$	≥ 0.01	≤ 1.5	20 to 150				
	two-stage TE-cooled (2TE), ~230	8	$\geq 2.5 \times 10^9$	$\geq 2.0 \times 10^9$	≥ 0.10	≤ 4	150 to 1000			TO8, TO66	wedged ZnSe AR coated
		10.6	$\geq 1.5 \times 10^9$	$\geq 1.0 \times 10^9$	≥ 0.05	≤ 3	90 to 350				
	three-stage TE-cooled (3TE), ~210	8	$\geq 4.0 \times 10^9$	$\geq 3.0 \times 10^9$	≥ 0.15	≤ 4	200 to 1500			TO8, TO66	wedged ZnSe AR coated
		10.6	$\geq 2.0 \times 10^9$	$\geq 1.5 \times 10^9$	≥ 0.10	≤ 3	100 to 400				
	four-stage TE-cooled (4TE), ~195	8	$\geq 8.0 \times 10^9$	$\geq 6.0 \times 10^9$	≥ 0.20	≤ 4	500 to 2000			TO8, TO66	wedged ZnSe AR coated
		10.6	$\geq 2.5 \times 10^9$	$\geq 2.0 \times 10^9$	≥ 0.15	≤ 3	120 to 500				

^{*)} Other optimal wavelengths available upon request.

^{**) Data sheet states minimum guaranteed D^* values for each detector model. Higher performance detectors can be provided upon request.}

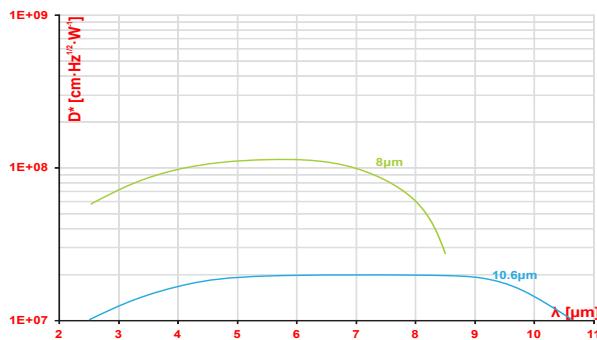
^{***)} Other optical area available upon request.

^{****)} Other windows available upon request.

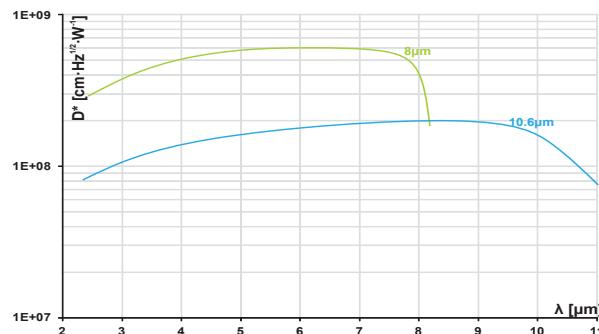


Spectral characteristics^{*)}

PVM

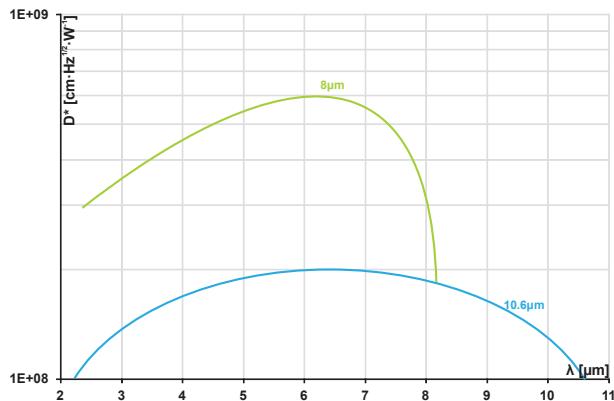


PVM-2TE

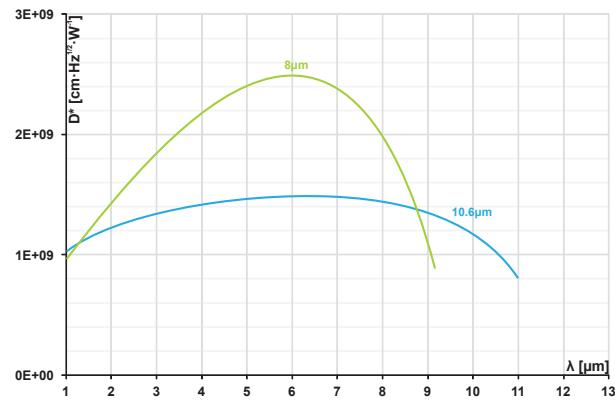


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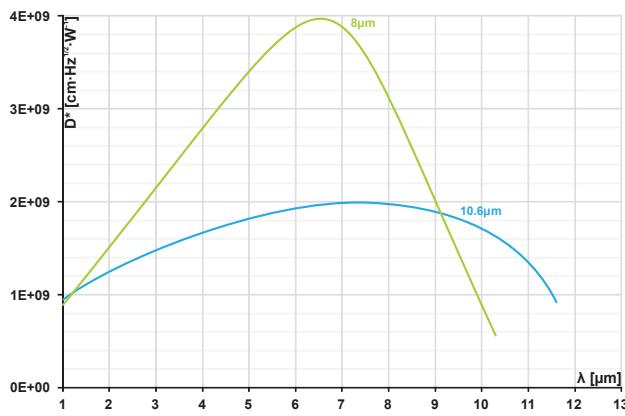
PVMI



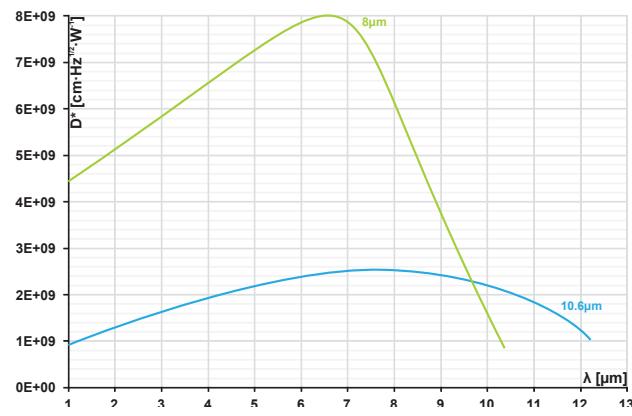
PVMI-2TE



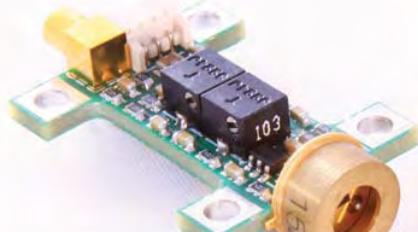
PVMI-3TE



PVMI-4TE



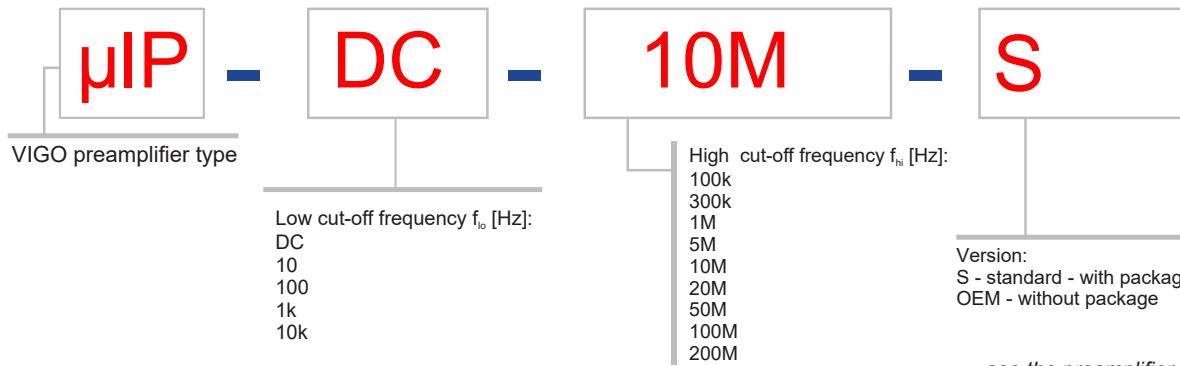
^{*)}Example of D* vs wavelength λ for HgCdTe detectors.
Spectral characteristics of individual detectors may vary from those shown on the chart.

μIP preamplifier

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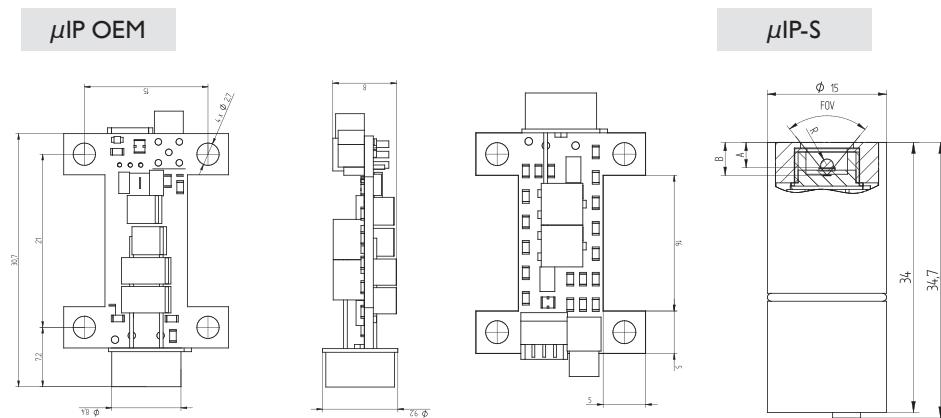
μIP is the transimpedance, AC or DC coupled, micro-size preamplifier. It is available in two versions: S – standard with package and O – OEM without package. μIP is intended to operation with either biased or non-biased uncooled detectors in TO39 package.

Code description

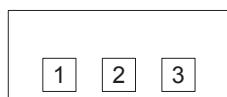


see the preamplifier specification table for additional information

Dimensions [mm]



Power supply connector - MOLEX 1x3 connector female



Pin number	Symbol	Function
1	$-V_{sup}$	power supply input (-)
2	GND	power ground
3	$+V_{sup}$	power supply input (+)

Preamplifier type	Main feature	Detector package	Detector type	Detector cooling	Radiator, cooling, TEC controlling	Input noise voltage density	Input noise current density	Low cut-off frequency
						$e_n \left[\frac{nV}{\sqrt{Hz}} \right]$	$i_n \left[\frac{pA}{\sqrt{Hz}} \right]$	$f_{lo} [Hz]$
VIP	standalone	BNC	PV, PVI, PVM, PVMI	uncooled	not needed	0.97 – 8.0 ¹⁾	0.02 – 3.5 ¹⁾	DC, 10, 100, 1k, 10k
μ IP	micro-size	TO39	PC, PCI, PV, PVI, PVM, PVMI	uncooled	not needed	0.97 – 8.0 ¹⁾	0.02 – 3.5 ¹⁾	DC, 10, 100, 1k, 10k
QIP	four-channel	TO8	PCQ, PVQ, PVMQ	uncooled	on board radiator and TEC controller, fan	0.97 – 8.0 ¹⁾	0.02 – 3.5 ¹⁾	DC, 10, 100, 1k, 10k
SIP	ultra-small, OEM	TO39 TO8	PC, PCI, PV, PVI, PVM, PVMI	uncooled 2TE, 3TE, 4TE	external heatsink needed	0.97 – 8.0 ¹⁾	0.02 – 3.5 ¹⁾	DC, 10, 100, 1k, 10k
FIP	very fast	TO8	PC, PCI, PV, PVI, PVM, PVMI	2TE, 3TE, 4TE	on board radiator, fan	1.1	5.0	1k, 10k
MIP	standard	TO8	PC, PCI, PV, PVI, PVM, PVMI	2TE, 3TE, 4TE	on board radiator, fan	0.97 – 8.0 ¹⁾	0.02 – 3.5 ¹⁾	DC, 10, 100, 1k, 10k
PIP	programmable	TO8	PC, PCI, PV, PVI, PVM, PVMI	2TE, 3TE, 4TE	on board radiator, fan	0.95	4.5 7.0	DC/10
AIP	on board TEC controller	TO8	PC, PCI, PV, PVI, PVM, PVMI	2TE, 3TE, 4TE	on board radiator and TEC controller, fan	0.97 – 8.0 ¹⁾	0.02 – 3.5 ¹⁾	DC, 10, 100, 1k, 10k

1) noise measurement frequency $f_0 = 10kHz$

2) first stage transimpedance = $1k\Omega$

3) first stage transimpedance = $5k\Omega$

4) transimpedance range $\frac{K_{imax}}{K_{imin}}$ up to 5 (dependent on f_{hi})

5) $f_{hi} \leq 1MHz$, load resistance $R_L = 1M\Omega$

6) $f_{hi} > 1MHz$, load resistance $R_L = 50M\Omega$

High cut-off frequency	Transimpedance	Output impedance	Output voltage swing	Output voltage offset	Power supply voltage	Power supply current	Supply connector	Signal output
$f_{hi}[\text{Hz}]$	$K_i \left[\frac{V}{A} \right]$	$R_{out}[\Omega]$	$V_{out}[V]$	$V_{off}[mV]$	$V_{sup}[V]$	$I_{sup}[mA]$		
100k, 300k, 1M, 5M, 10M, 20M	fixed up to 1.0×10^5	50	$\pm 10^{5j}$ $\pm 2^{6j}$	max $\pm 20^{9j}$	$\pm 15^{12j}$ $\pm 9^{13j}$	max ± 25	DB9	BNC
100k, 300k, 1M, 5M, 10M, 100M, 200M	fixed up to 1.0×10^5	50	$\pm 2^{5j}$ $\pm 1^{6j}$	max $\pm 20^{9j}$	± 9	max ± 50	MOLEX1x3	MMCX
100k, 300k, 1M, 5M, 10M, 100M	fixed up to 2.0×10^5	50	$\pm 2^{5j}$ $\pm 1^{6j}$	max $\pm 20^{9j}$	+5	max ± 50	DC 2.1/5.5	4xMCX
100k, 300k, 1M, 5M, 10M, 100M, 250M	tunable ^{4j} up to 1.0×10^5	50	$\pm 10^{5j}$ $\pm 1^{6j}$	max $\pm 20^{9j}$	$\pm 15^{12j}$ $\pm 9^{13j}$	max ± 50	AMP2x4	MMCX
1G	fixed up to 8.5×10^3	50	± 1	-	+12/-5	+100 -50	LEMO	SMA (DC monitor as an option)
100k, 300k, 1M, 5M, 10M, 100M, 250M	fixed up to 2.0×10^5	50	$\pm 10^{5j}$ $\pm 2^{7j}$ $\pm 1^{8j}$	max $\pm 20^{9j}$	$\pm 15^{12j}$ $\pm 9^{13j}$	max ± 50	LEMO	SMA
150k/1.5M/20M 1.5M/15M/200M	digitally adjustable 500 – 30k ^{2j} 2.5k – 150k ^{3j}	50	± 1	max $\pm 20^9$ (DC) max ± 10 (AC)	± 9	typ ± 80 max ± 100	LEMO	SMA
100k, 300k, 1M, 5M, 10M, 100M, 250M	fixed up to 2.0×10^5	50	$\pm 2^{5j}$ $\pm 1^{6j}$	max $\pm 20^{9j}$	+5 ^{10j} +12 ^{11j}	max ± 50	DC 2.1/5.5	2xSMA (DC monitor as an option)

⁷⁾ $1\text{MHz} < f_{hi} \leq 20\text{MHz}$, load resistance $R_L = 1\text{M}\Omega$

⁸⁾ $20\text{MHz} < f_{hi} \leq 250\text{MHz}$, load resistance $R_L = 50\text{M}\Omega$

⁹⁾ Measured with equivalent resistor at the input instead of the detector. It's to avoid the environmental thermal radiation's impact

¹⁰⁾ with uncooled, 2TE and 3TE detectors

¹¹⁾ with 4TE detectors

¹²⁾ $f_{hi} \leq 1\text{MHz}$

¹³⁾ $f_{hi} > 1\text{MHz}$

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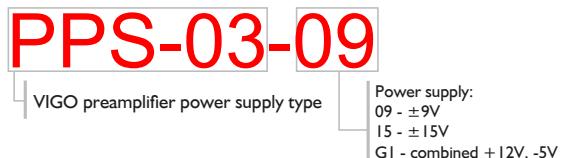


PPS-03 is a small size preamplifier power supply, designed to operate with VIGO IR detection modules with uncooled detectors (VIP, SIP-TO39, uIP)

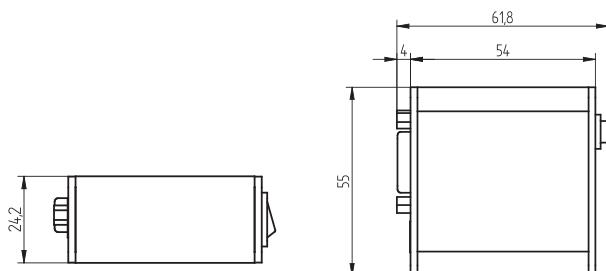
Specification

Parameter	Value
Power supply voltage V_{sup} [V AC]	100 to 240 (50Hz to 60Hz)
Output voltage [V DC]	$\pm 15, \pm 9, +12, -5$
Output current [mA]	± 100
Weight [g]	100

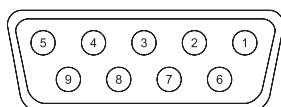
Code description



Dimensions [mm]



Power supply connector - DB9 connector female



Pin number	Symbol	Function
1	N.C.	not connected
2	N.C.	not connected
3	GND	power ground
4	N.C.	not connected
5	N.C.	not connected
6	$-V_{sup}$	power supply output (-)
7	N.C.	not connected
8	N.C.	not connected
9	$+V_{sup}$	power supply output (+)
metal cover	GND-SH	shield